

#3

L Number	Hits	Search Text	DB	Time stamp
1	5971	((428/332) or (427/255.18) or (427/579) or (118/723E) or (118/724)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/03 14:53
2	71	(organosilicate TEOS tetraethylorthosilicate) and susceptor and (((428/332) or (427/255.18) or (427/579) or (118/723E) or (118/724)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/03 14:54
3	23	thickness and (TEOS silicate organosilicate) and "flat panel" and (((428/332) or (427/255.18) or (427/579) or (118/723E) or (118/724)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/03 14:54
4	49	(TEOS with sccm) and (((428/332) or (427/255.18) or (427/579) or (118/723E) or (118/724)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/03 14:55
-	424	(organosilicate TEOS tetraethylorthosilicate) and susceptor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/03 14:54
-	297	((organosilicate TEOS tetraethylorthosilicate) and susceptor) and (uniform uniformity)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/01 18:56
-	283	((organosilicate TEOS tetraethylorthosilicate) and susceptor) and (uniform uniformity) and temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/01 18:55
-	64	(organosilicate TEOS tetraethylorthosilicate).ab. and susceptor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/01 18:55
-	29	((organosilicate TEOS tetraethylorthosilicate).ab. and susceptor) and (uniform uniformity)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/01 18:56
-	66	((organosilicate TEOS tetraethylorthosilicate) and susceptor) and (thickness with temperature)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/02 08:06
-	772	"organosilicate"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/02 08:06
-	92	"organosilicate".clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/02 08:06
-	34	"organosilicate".clm. and 1.ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/02 08:08
-	158	"flat panel" and susceptor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/02 08:09

-	11	("flat panel" and susceptor) and ("organosilicate" TEOS)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/02 09:05
-	426	TEOS with sccm	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/03 14:54
-	59	(TEOS with sccm) with "800"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/02 09:07
-	15	((TEOS with sccm) with "800") with (He helium) with (oxygen "O.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/02 09:07
-	90	(TEOS with sccm) with "300"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/02 09:07
-	13	((TEOS with sccm) with "300") with (He helium) with (oxygen "O.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/02 09:33
-	10	"power density" with SCCM with TEOS	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/02 10:25
-	445	"300 mm wafers"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/03 10:10
-	644	thickness and (TEOS silicate organosilicate) and "flat panel"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/03 14:54
-	183	(thickness with (variation deviation uniformity uniform)) and (TEOS silicate organosilicate) and "flat panel"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/03 14:52